

forming a photosensitive film pattern on said nitride film;
etching said nitride film by using said photosensitive film pattern as a mask to expose the insulating layer; and
etching said exposed insulating layer.

27. (New) A method of making a semiconductor device as claimed in Claim 26, wherein said etching step is performed by an isotropic etching method or a mixed method of anisotropic etching and isotropic etching.

28. (New) A method of making a semiconductor device as claimed in Claim 25, wherein said lower conductive lines are slanted longitudinally along said groove.

29. (New) A method of making a semiconductor device as claimed in Claim 25, further comprises the steps of:

forming a second insulating layer on the surface of said lower conductive lines;
covering the surface of said substrate including said second insulating layer with an oxidization prevention layer; and
burying a buried material between said upper conductive lines in said groove.

30. (New) A method of making a semiconductor device as claimed in Claim 29, wherein said buried material is a flux material such as spin on glass.

31. (New) A method of making a semiconductor device as claimed in Claim 30, wherein said buried material is buried until said oxidization prevention layer is exposed when said flux material is etched back.

32. (New) A method of making a semiconductor device as claimed in Claim 29, further comprising the step of forming a contact region by etching said second insulating layer and said oxidization prevention layer for connecting said upper and lower conductive lines.

33. (New) A method of making a semiconductor device as claimed in Claim 29, wherein said second insulating layer is formed by oxidizing said lower conductive lines.

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34. (New) A method of making a semiconductor device as claimed in Claim 29, wherein an oxide film is formed on said lower conductive lines.

35. (New) A method of making a semiconductor device as claimed in Claim 25, wherein said step of forming said cylindrical insulator comprises the steps of:
filling said groove with an oxidizable material; and
oxidizing said oxidizable material.

36. (New) A method of making a semiconductor device as claimed in Claim 35, wherein said step of filling said groove with an oxidizable material comprises the steps of:
laminating an oxidizable material on the entire surface of said substrate; and
etching said oxidizable materials.

37. (New) A method of making a semiconductor device as claimed in Claim 36, wherein said oxidizable material is polysilicon or amorphous silicon.

38. (New) A method of making a semiconductor device as claimed in Claim 36, wherein said oxidizable material is etched by a CMP process.

39. (New) A method of making a semiconductor device as claimed in Claim 36, wherein said step of etching said oxidizable material is performed by an etch-back method.

40. (New) A method of making a semiconductor device as claimed in Claim 25, wherein said upper and lower conductive lines are slanted longitudinally along the groove in opposite directions.

41. (New) A method of making a semiconductor device including an inductor, comprising the steps of:

forming a groove in an insulating layer on a semiconductor substrate;
forming lower conductive lines across the groove;
forming a magnetic core above said lower conductive lines and aligned with said groove; and
forming upper conductive lines over said magnetic core;
electrically coupling said upper conductive lines to said lower conductive lines.

42. (New) A method of making a semiconductor device as claimed in Claim 41, wherein said step of forming the groove comprises the steps of:

- forming an oxide film as a relief region on said substrate;
- forming a silicon nitride layer and a high temperature oxide film on said oxide film;
- forming a trench by etching said oxide film, silicon nitride layer and high temperature oxide film;
- forming an second oxide film on the entire surface of said substrate;
- forming an groove having a semicircular cross-section by wet-etching said second oxide film; and
- removing said oxide film, silicon nitride layer and high temperature oxide film.

43. (New) A method of making a semiconductor device as claimed in Claim 41, wherein said step of forming lower conductive lines comprises the steps of:

- forming an oxide film on the entire surface of said substrate;
- forming a conductive material on said oxide film; and
- by patternizing said conductive material.

44. (New) A method of making a semiconductor device as claimed in Claim 41, wherein said lower conductive lines are formed across said groove with a predetermined distance therebetween.

45. (New) A method of making a semiconductor device as claimed in Claim 43, wherein said lower conductive lines are made of aluminum or copper.

46. (New) A method of making a semiconductor device as claimed in Claim 41, wherein said step of forming said magnetic core comprises the steps of:

- forming an oxide film over said lower conductive lines;
- forming a magnetic material over said oxide film;
- forming a capping oxide layer over said magnetic material;
- patternizing said magnetic material; and
- forming a spacer at each side of said magnetic core, thereby wrapping said magnetic core with oxide.

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47. (New) A method of making a semiconductor device as claimed in Claim 41, wherein said upper conductive lines are formed across the core and slanted longitudinally along the core with a predetermined distance therebetween.

48. (New) A method of making a semiconductor device as claimed in Claim 47, wherein said lower conductive lines are made of aluminum or copper.

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